

## Positive Synchrotron Resists AR-P 6500

### AR-P 6510 e-beam resists for high film thicknesses

Thick positive resists for the production of microcomponents

#### Characterisation

- e-beam, synchrotron, X-ray  
(no yellow light required)
- excellent image quality
- solvent-based developer
- film thickness values of 10 µm to 250 µm
- process-stable
- high molecular weight poly(methyl methacrylate)
- safer solvent PGMEA

#### Film thickness values

2 min / 30 s	6510.17	6510.18	6510.19
200 / 350 rpm	95 µm	155 µm	235 µm
350 / 500 rpm	56 µm	88 µm	135 µm

These resists are designed for high film thicknesses which can only be obtained with low spin speeds. At spin numbers of < 1000 rpm, resists tend to form strings (candy floss effect). Thinner films can be realised if dilutions are used.

#### Structure resolution



AR-P 6510.17  
Film thickness 40 µm, structures up to 5 µm (synchrotron)

#### Process parameters

Substrate	Si 4" waver
Tempering	100 °C, 4 h, convection oven
Belichtung	Synchrotron
Development	AR 600-51, 20 min
Stopper	AR 600-61, 3 min

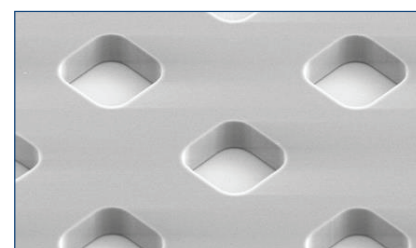
#### Properties I

Parameter / AR-P 6510.	17	18	19
Solids content (%)	17	18	19
Viscosity 25 °C (mPas)	24.500	41.000	60.500
Film thickness/200 rpm (µm)	95	155	235
Resolution best value (µm)	1 µm (X-Ray)		
Contrast	10 (X-Ray)		
Flash point (°C)	42		
Storage 6 month (°C)	6		

#### Properties II

Glass trans. temperature (°C)	105	
Dielectric constant	2.6	
Cauchy coefficients	N <sub>0</sub>	1.480
	N <sub>1</sub>	41.9
	N <sub>2</sub>	0
Plasma etching rates (nm/min) (5 Pa, 240-250 V Bias)	Ar-sputtering	22
	O <sub>2</sub>	350
	CF <sub>4</sub>	61
	80 CF <sub>4</sub> + 16 O <sub>2</sub>	169

#### Resist structures



AR-P 6510.17 (diluted),  
exposure with e-beam  
(developer AR 600-55),  
film thickness 5 µm


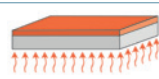
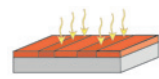
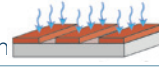
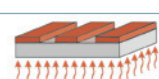
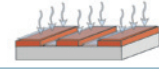

#### Process chemicals

Adhesion promoter	AR 300-80
Developer	AR 600-51
Thinner	AR 300-12
Stopper	AR 600-61
Remover	AR 600-71, AR 300-76

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### Process conditions

This diagram shows exemplary process steps for AR-P 6500 resists. All specifications are guideline values which have to be adapted to own specific conditions. For further information on processing, see "Detailed instructions for optimum processing of e-beam resists". For recommendations on waste water treatment and general safety instructions, see "General product information on Allresist e-beam resists".

Coating		AR-P 6510.17 350 rpm, 5 min 45 µm
Tempering (± 1 °C)		95 °C, 60 min hot plate (temperature ramps recommended) 90 °C, 3 h convection oven (temperature ramps recommended)
E-beam exposure		Synchrotron accelerator Exposure dose (E <sub>0</sub> ): 4 kJ/cm <sup>3</sup>
Development (21-23 °C ± 1 °C) Immersion		AR 600-51 15 min
Stopping / Rinse		AR 600-61, 30 s / DI-H <sub>2</sub> O, 30 s
Post-bake (optional)		100 °C, 10 min hot plate or 95 °C, 60 min, convection oven for complete drying and slightly enhanced plasma etching resistance
Customer-specific technologies		LIGA procedures or the fabrication of X-ray masks
Removal		AR 300-76 or O <sub>2</sub> plasma ashing

### Processing instructions for coating

Prior to spin coating it is recommended to remove gases which may possibly be present. The highly viscous resist should therefore rest a few hours before use. A warming of resist bottles in a water bath to 50 °C max. to reduce the viscosity and the utilisation of ultrasound support the removal of gas bubbles. Resist deposition should be performed as carefully as possible to avoid any additional introduction of air bubbles. Slow spin speeds and low exposure times are advantageous (200 to 350 rpm, > 3 min). Edge bead formation can be reduced if the rotational speed is briefly increased towards the end of the coating procedure (for 10 s to max. 500 rpm). The amount of resist will also influence the film thickness; for 4 inch-wafers, the use of at least 10 g of resist are recommended. In order to obtain optimum film qualities, own experiments of each user are required.